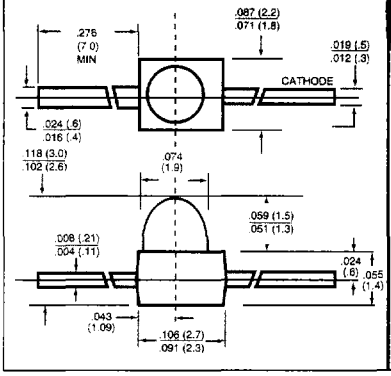
T-3/4



Part Number (Emitters)	Emission Angle 1/2 Power	Radiant Intensity min	max	units	V_F/I_F V/(mA) max	I_R/V_R (μA)/(V) max	Notes
940 nm GaAs							
QEB363	±12°	8	—	mW/sr	1.6/20	100/5	1,3
880 nm AlGaAs							
QEB373	±12°	16	—	mW/sr	1.7/20	100/5	1

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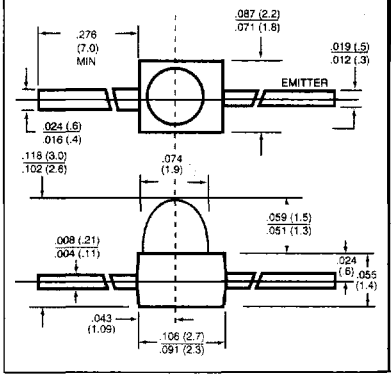

Part Number (Sensors)	Reception Angle 1/2 Sensitivity	Light min	max	units	BV_{CEO} (V) min	I_{CEO}/V_{CE} (nA)/(V) max	Notes
Phototransistor							
QSB363	±12°	0.7	—	mA	30	100/10	2

Notes

1. I_e @ I_F = 100 mA pulsed
2. On-State Collector Current @ E_e = 0.5 mW/cm² (AlGaAs), V_{CE} = 5 V
3. Reverse Polarity

Maximum Ratings Table E (Applies to all components on this page.)

Storage Temperature	–40 to +85° C
Operating Temperature	–40 to +85° C
Soldering:	
Lead Temperature (Iron)	240° C for 5 s
Lead Temperature (Flow)	260° C for 10 s
QEB	
Continuous Forward Current	50 mA
Reverse Voltage	5.0 V
Power Dissipation	100 mW
Derate linearly at 1.33 mW/° C above 25° C	
QSB	
Collector-Emitter Breakdown Voltage	30 mA
Emitter-Collector Breakdown Voltage	5.0 V
Power Dissipation	100 mW
Derate linearly at 1.33 mW/° C above 25° C	